U.S. PATENT DOCUMENTS

4,926,074	A	5/1990	Singer et al.
4,926,243	A	5/1990	Nakagawa et al.
4,929,987	A	5/1990	Einthoven
4,939,566	A	7/1990	Singer et al.
4,963,951	A	10/1990	Adler et al.
4,967,246	A	10/1990	Tanaka
5,010,024	A	4/1991	Allen et al.
5,025,296	A	6/1991	Fullerton et al.
5,040,045	A	8/1991	McArthur et al.
5,068,700	A	11/1991	Yamaguchi et al.
5,072,266	A	12/1991	Belucea et al.
5,122,848	A	6/1992	Lee et al.
5,146,298	A	9/1992	Eklund
5,155,574	A	10/1992	Yamaguchi
5,237,193	A	8/1993	Williams et al.
5,258,636	A	11/1993	Rumennik et al.
5,270,264	A	12/1993	Andideh et al.
5,294,824	A	3/1994	Okada
5,306,656	A	4/1994	Williams et al.
5,313,082	A	5/1994	Eklund
5,324,683	A	6/1994	Fitch et al.
5,326,711	A	7/1994	Malhi
5,349,225	A	9/1994	Redwine et al.
5,359,221	A	10/1994	Miyamoto et al.
5,386,136	A	1/1995	Williams et al.
5,438,215	A	8/1995	Tihanyi
5,473,180	A	12/1995	Ludikhuize
5,514,608	A	5/1996	Williams et al.
5,521,105	A	5/1996	Hsu et al.
5,550,405	A	8/1996	Cheung et al.
5,637,898	A	6/1997	Baliga
5,648,283	A	7/1997	Tsang et al.
5,654,206	A	8/1997	Merrill
5,656,543	A	8/1997	Chung
5,659,201	A	8/1997	Wollensen
5,663,599	A	9/1997	Lur
5,665,994	A	9/1997	Palara
5,670,828	A	9/1997	Cheung et al.
5,679,608	A	10/1997	Chevy et al.
5,716,887	A	2/1998	Kim
5,760,440	A	6/1998	Kitamura et al.
5,821,144	A	10/1998	D'Anna et al.
5,869,875	A	2/1999	Herbert
5,917,216	A	6/1999	Floyd et al.
5,929,481	A	7/1999	Hshieh et al.
5,943,595	A	8/1999	Akiyama et al.
5,969,408	A	10/1999	Perelli
5,973,360	A	10/1999	Tihanyi
5,998,833	A	12/1999	Baliga
6,010,926	A	1/2000	Rho et al.
6,049,108	A	4/2000	Williams et al.
6,054,752	A	4/2000	Hara et al.
6,084,277	A	7/2000	Disney et al.
6,127,703	A	10/2000	Letavic et al.
6,133,607	A	10/2000	Funaki et al.
6,184,555	B1	2/2001	Tihanyi et al.
6,191,447	B1	2/2001	Baliga
6,194,283	B1	2/2001	Gardner et al.
6,207,994	B1	3/2001	Rumennik et al.
6,294,818	B1	9/2001	Fujihira
6,316,807	B1	11/2001	Fujishima et al.
6,353,252	B1	3/2002	Yasuhara et al.
6,359,308	B1	3/2002	Hijzen et al.
6,362,064	B2	3/2002	McGregor et al.
6,365,932	B1	4/2002	Kouno et al.
6,388,286	B1	5/2002	Baliga
6,404,009	B1	6/2002	Mori et al.
6,462,377	B2	10/2002	Hurky et al.
6,468,847	B1	10/2002	Disney
6,509,220	B2	1/2003	Disney
6,525,372	B2	2/2003	Baliga
6,555,873	B2 *	4/2003	Disney et al. 257/342
6,573,558	B2	6/2003	Disney
6,635,544	B2	10/2003	Disney
6,667,213	B2	12/2003	Disney
6,677,641	B2	1/2004	Kocon
6,683,346	B2	1/2004	Zeng
6,734,714	B2	5/2004	Disney
6,764,889	B2	7/2004	Baliga
6,781,194	B2	8/2004	Baliga
6,781,198	B2	8/2004	Disney
6,787,847	B2	9/2004	Disney et al.
6,787,848	B2	9/2004	Ono et al.
6,809,354	B2	10/2004	Okada et al.
6,825,536	B2	11/2004	Disney
6,838,346	B2	1/2005	Disney
6,865,093	B2	3/2005	Disney
6,882,005	B2	4/2005	Disney et al.
6,987,299	B2	1/2006	Disney et al.
7,115,958	B2	10/2006	Disney et al.
7,135,748	B2	11/2006	Balakrishnan
7,335,944	B2	2/2008	Banerjee
2001/0015459	A1	8/2001	Watanabe et al.
2002/0056884	A1	5/2002	Baliga
2002/0175351	A1	11/2002	Baliga
2003/0209757	A1	11/2003	Henninger et al.

FOREIGN PATENT DOCUMENTS

EP	1073 123	A2	7/2000
GB	2 309 336	A	1/1997
JP	56-38867		4/1981
JP	57-10975		1/1982
JP	57-12557		1/1982
JP	57-12558		1/1982
JP	60-64471	A	4/1985
JP	1-238037		9/1989
JP	3-211771		9/1991
JP	4107877	A	4/1992
JP	04-107867		7/1992
JP	6-120510		4/1994
JP	6-196630		6/1994
JP	6-224426		8/1994
JP	9-266311		10/1997
JP	2000-12854		1/2000
JP	2002-43562		2/2002
WO	WO 97/35346		9/1997
WO	WO 99/34449		7/1999
WO	WO 00/33385		6/2000
WO	WO 02/41402	A2	5/2002
WO	WO 02/099909	A1	12/2002

OTHER PUBLICATIONS

"Realization of High Breakdown Voltage (>700V) in Thin SOI Devices," S. Merchant, et al, Phillips Laboratories North America, 1991 IEEE, pp. 31-35.

"Theory of Semiconductor Superjunction Devices," Tatsuhiko Fujihira, Japan Journal of Applied Physics vol. 36, Oct. 1997, pp. 6254-6262.

"Air-Gap Formation During IMD Deposition to Lower Interconnect Capacitance," B. Shieh et al, IEEE Electron Device Letters vol. 17 No. 1, Jan. 1998.

IEEE Electron Devices Letters, vol. 22, No. 8, Aug. 8, 2001, pp. 407-409.

"Comparison of High-Voltage Devices for Power Integrated Circuits," R. Jayaraman et al, IEDM 84, pp. 258-261.

"A New Generation of High-Voltage MOSFETs Breaks the Limit Line of Silicon " Deboy et al. Siemens AG, Munchen, Germany, IEDM 98 pp. 683-685.

"High Performance 600V Smart Power Technology Based on Thin Layer Silicon-on-Insulators," T. Letavic, et al, Phillips Research, 4 pages.

"Modern Semiconductor Device Physics," Sze, et al, John Wiley & Sons, Chapter 4 ("Power Devices"), 1998, pp. 203-206.